

FIG. 1E



**Detected Number** 

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DEVICE

Bit Number/µm 550°CSPC+LC620mf
FPM 10min Etching
Parameter 175 Points
Average: 1.21
Standard Deviation: 2.1

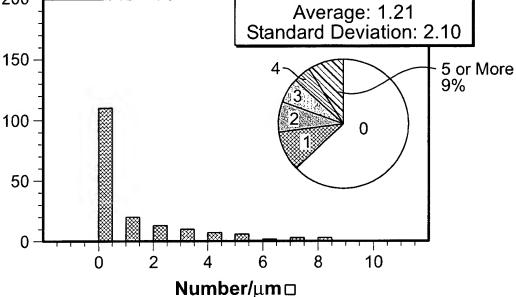
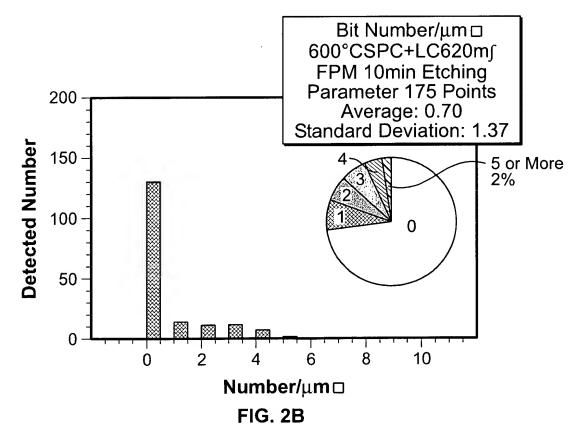


FIG. 2A

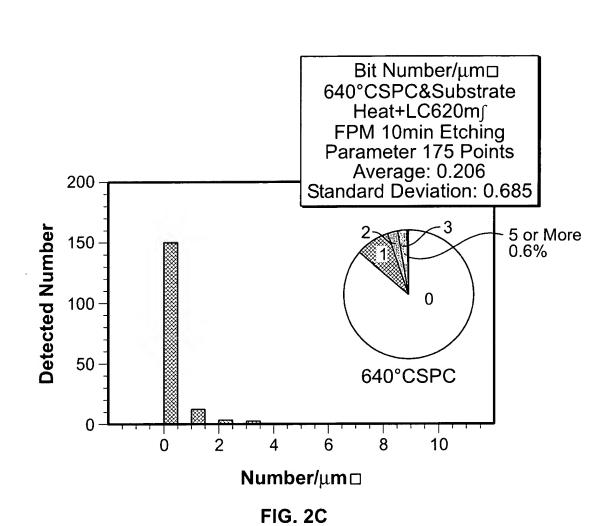


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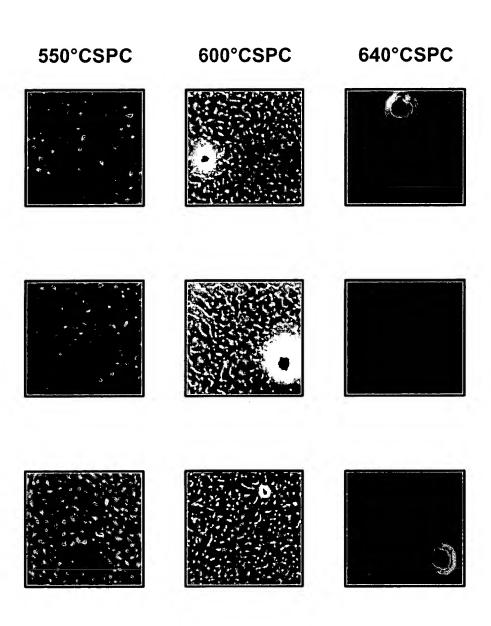
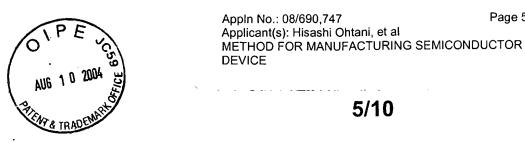
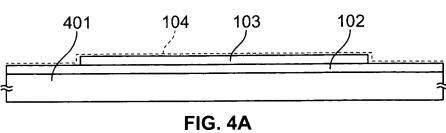
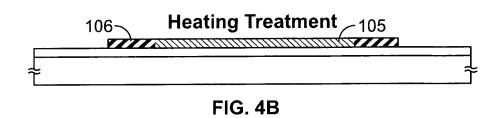


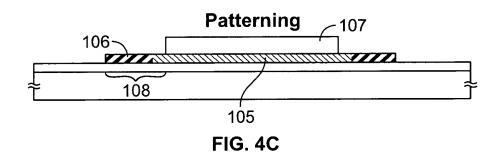
FIG. 3

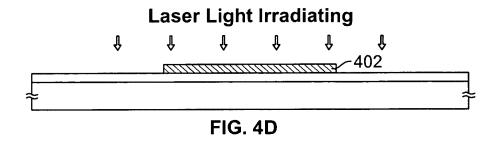


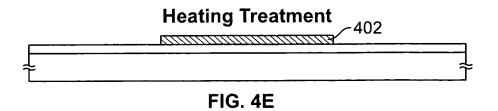


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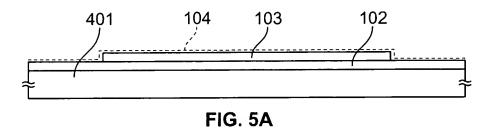


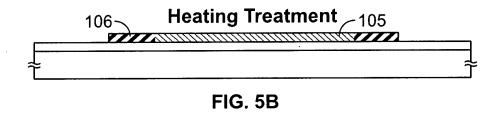


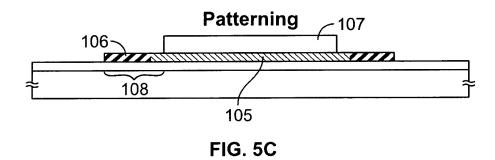
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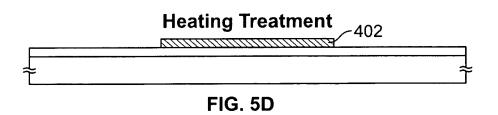
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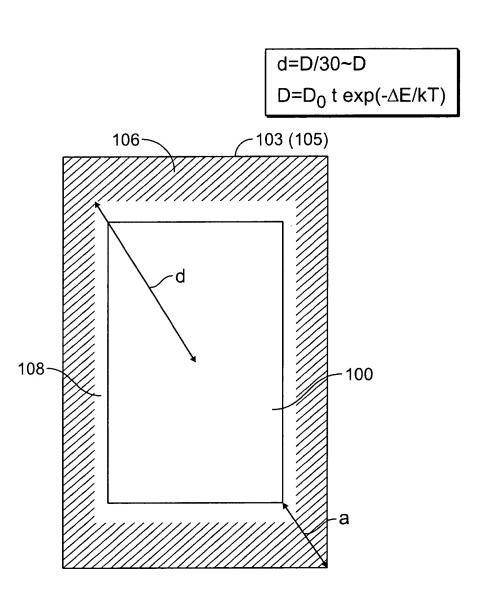


FIG. 6

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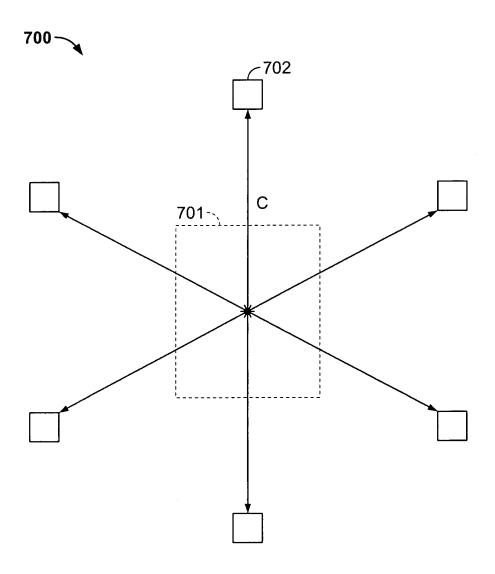
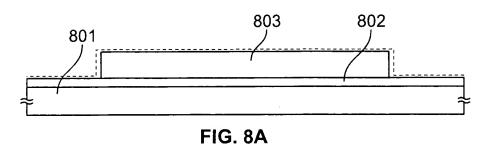


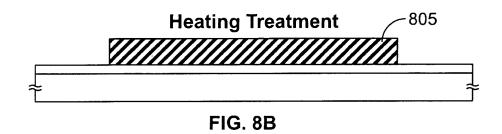
FIG. 7

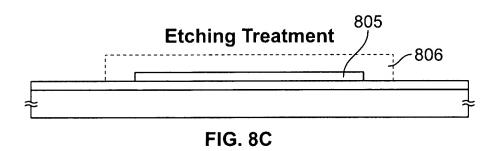


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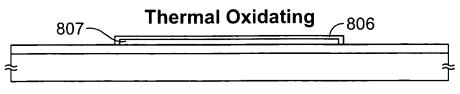
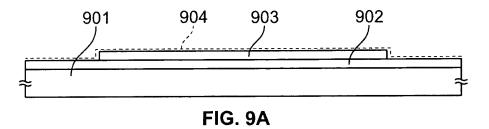


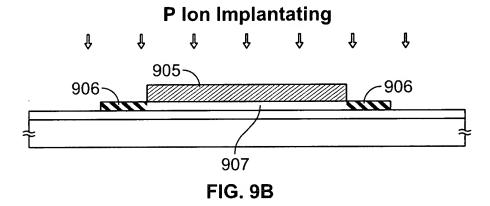
FIG. 8D

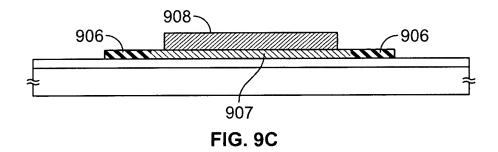


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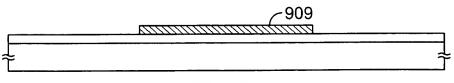


FIG. 9D